

6N SILICON MATERIAL SPECIFICATIONS

Specifications:

1. Crystal growth method: CZ
2. Growing Direction: 100
3. Conductive type, Dopant: P-type, B
4. Resistivity: 0.5~6Ω.cm
5. Lifetime: ≥8us
6. Etch-pit density: ≤30000/cm²
7. Oxygen content: ≤1.0x10¹⁸at/cm³
8. Carbon content: ≤5.0x10¹⁶at/cm³

Analysis Report

Element	(ppmwt)	Element	(ppmwt)	Element	(ppmwt)
Hf	<0.01	Ad	<0.1	Ho	<0.005
Al	<0.01	Hg	<0.1	Rh	<0.005
Ru	<0.01	Re	<0.01	Ag	<0.01
Al	<0.05	I	<0.01	S	<0.05
B	<0.5	In	<0.01	Sb	<0.05
Ir	<0.01	Ba	<0.005	Th	<0.001
Be	<0.005	K	<0.05	Se	<0.05
Bi	<0.01	Br	<0.05	Si	Matric
La	<0.005	Li	<0.01	Sm	<0.005
C	<0.1	Lu	<0.005	Sn	<0.05
Ca	<0.05	Mg	<0.05	Tb	<0.005
Mo	<0.05	Mn	<0.01	Ta	Source
Ce	<0.005	Cd	<0.1	Sr	<0.01
Cl	<0.01	Co	<0.01	Te	<0.05
N	<0.01	Na	<0.01	Sr	<0.05
Cr	<0.1	Nb	<0.01	Ti	<0.01
Cs	<0.005	Tl	<0.01	Nd	<0.005
Cu	<0.01	Ni	<0.01	Tm	<0.005
Os	<0.01	O	<9	U	<0.005
Er	<0.005	Dy	<0.005	V	<0.01
Eu	<0.006	P	<0.5	Au	<0.05
F	<0.05	Pb	<0.05	Y	<0.01
Fe	<0.01	Zn	<0.05	Yb	<0.005
Ga	<0.005	Gc	<0.005	Pd	<0.01
Pr	<0.005	Pt	<0.01	Zr	<0.01
Ge	<0.05	Rb	<0.05	W	<0.01
Gd	<0.05				

Note: Above testing results are analysis by ICP-MS and ICP-AES and subject the samples only.

Sales Dept. Information:

Please contact our sales dept. as per the following information:

Tel: (86-10) 82070680

Fax: (86-10) 82070690

E-Mail: sales@sinosi.com

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